Freescale Semiconductor - MPC8347VRADDB Datasheet

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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Active
Core Processor	PowerPC e300
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	266MHz
Co-Processors/DSP	-
RAM Controllers	DDR
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (2)
SATA	-
USB	USB 2.0 + PHY (2)
Voltage - I/O	2.5V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	-
Package / Case	620-BBGA Exposed Pad
Supplier Device Package	620-HBGA (29x29)
Purchase URL	https://www.e-xfl.com/pro/item?MUrl=&PartUrl=mpc8347vraddb

1 Overview

This section provides a high-level overview of the MPC8347E features. Figure 1 shows the major functional units within the MPC8347E.

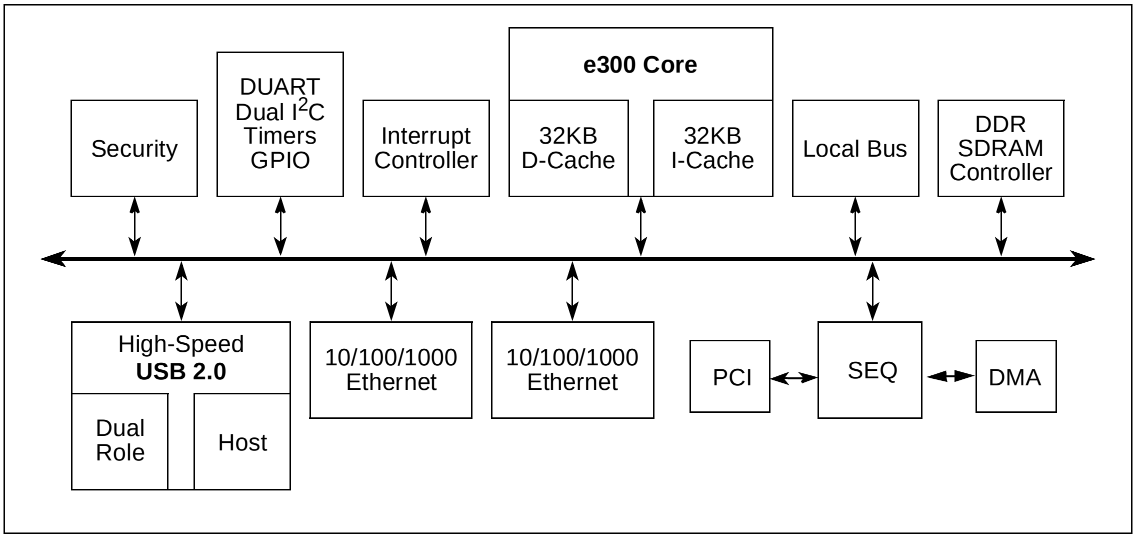


Figure 1. MPC8347E Block Diagram

Major features of the MPC8347E are as follows:

- Embedded PowerPC e300 processor core; operates at up to 667 MHz
  - High-performance, superscalar processor core
  - Floating-point, integer, load/store, system register, and branch processing units
  - 32-Kbyte instruction cache, 32-Kbyte data cache
  - Lockable portion of L1 cache
  - Dynamic power management
  - Software-compatible with the other Freescale processor families that implement Power Architecture technology
- Double data rate, DDR SDRAM memory controller
  - Programmable timing for DDR-1 SDRAM
  - 32- or 64-bit data interface, up to 333-MHz data rate for TBGA, 266 MHz for PBGA
  - Four banks of memory, each up to 1 Gbyte
  - DRAM chip configurations from 64 Mbit to 1 Gbit with x8/x16 data ports
  - Full error checking and correction (ECC) support
  - Page mode support (up to 16 simultaneous open pages)
  - Contiguous or discontiguous memory mapping
  - Read-modify-write support
  - Sleep mode for self-refresh SDRAM
  - Auto refresh

2 Electrical Characteristics

This section provides the AC and DC electrical specifications and thermal characteristics for the MPC8347E. The MPC8347E is currently targeted to these specifications. Some of these specifications are independent of the I/O cell, but are included for a more complete reference. These are not purely I/O buffer design specifications.

2.1 Overall DC Electrical Characteristics

This section covers the ratings, conditions, and other characteristics.

2.1.1 Absolute Maximum Ratings

Table 1 provides the absolute maximum ratings.

Table 1. Absolute Maximum Ratings[1]

Characteristic		Symbol	Max Value	Unit	Notes
Core supply voltage		V_{DD}	–0.3 to 1.32	V	
PLL supply voltage		AV_{DD}	–0.3 to 1.32	V	
DDR DRAM I/O voltage		GV_{DD}	–0.3 to 3.63	V	
Three-speed Ethernet I/O, MII management voltage		LV_{DD}	–0.3 to 3.63	V	
PCI, local bus, DUART, system control and power management, I^2C, and JTAG I/O voltage		OV_{DD}	–0.3 to 3.63	V	
Input voltage	DDR DRAM signals	MV_{IN}	–0.3 to (GV_{DD} + 0.3)	V	2, 5
	DDR DRAM reference	MV_{REF}	–0.3 to (GV_{DD} + 0.3)	V	2, 5
	Three-speed Ethernet signals	LV_{IN}	–0.3 to (LV_{DD} + 0.3)	V	4, 5
	Local bus, DUART, CLKIN, system control and power management, I^2C, and JTAG signals	OV_{IN}	–0.3 to (OV_{DD} + 0.3)	V	3, 5
	PCI	OV_{IN}	–0.3 to (OV_{DD} + 0.3)	V	6
Storage temperature range		T_{STG}	–55 to 150	°C	

Notes:

[1] Functional and tested operating conditions are given in Table 2. Absolute maximum ratings are stress ratings only, and functional operation at the maximums is not guaranteed. Stresses beyond those listed may affect device reliability or cause permanent damage to the device.

[2] **Caution:** MV_{IN} must not exceed GV_{DD} by more than 0.3 V. This limit can be exceeded for a maximum of 20 ms during power-on reset and power-down sequences.

[3] **Caution:** OV_{IN} must not exceed OV_{DD} by more than 0.3 V. This limit can be exceeded for a maximum of 20 ms during power-on reset and power-down sequences.

[4] **Caution:** LV_{IN} must not exceed LV_{DD} by more than 0.3 V. This limit can be exceeded for a maximum of 20 ms during power-on reset and power-down sequences.

[5] (M,L,O)V_{IN} and MV_{REF} may overshoot/undershoot to a voltage and for a maximum duration as shown in Figure 2.

[6] OV_{IN} on the PCI interface can overshoot/undershoot according to the PCI Electrical Specification for 3.3-V operation, as shown in Figure 3.

2.1.2 Power Supply Voltage Specification

Table 2 provides the recommended operating conditions for the MPC8347E. Note that the values in Table 2 are the recommended and tested operating conditions. Proper device operation outside these conditions is not guaranteed.

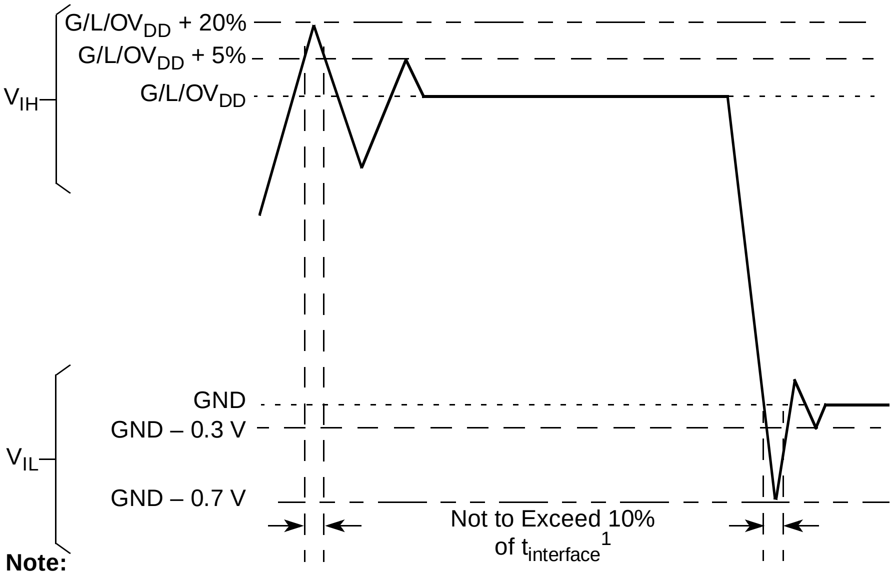
Table 2. Recommended Operating Conditions

Characteristic	Symbol	Recommended Value	Unit	Notes
Core supply voltage	V_{DD}	1.2 V ± 60 mV	V	1
PLL supply voltage	AV_{DD}	1.2 V ± 60 mV	V	1
DDR DRAM I/O supply voltage	GV_{DD}	2.5 V ± 125 mV	V	
Three-speed Ethernet I/O supply voltage	LV_{DD1}	3.3 V ± 330 mV 2.5 V ± 125 mV	V	
Three-speed Ethernet I/O supply voltage	LV_{DD2}	3.3 V ± 330 mV 2.5 V ± 125 mV	V	
PCI, local bus, DUART, system control and power management, I^2C, and JTAG I/O voltage	OV_{DD}	3.3 V ± 330 mV	V	

Note:

[1] GV_{DD}, LV_{DD}, OV_{DD}, AV_{DD}, and V_{DD} must track each other and must vary in the same direction—either in the positive or negative direction.

Figure 2 shows the undershoot and overshoot voltages at the interfaces of the MPC8347E.



Note:
1. $t_{interface}$ refers to the clock period associated with the bus clock interface.

Figure 2. Overshoot/Undershoot Voltage for $GV_{DD}/OV_{DD}/LV_{DD}$

6.2 DDR SDRAM AC Electrical Characteristics

This section provides the AC electrical characteristics for the DDR SDRAM interface.

6.2.1 DDR SDRAM Input AC Timing Specifications

Table 13 provides the input AC timing specifications for the DDR SDRAM interface.

Table 13. DDR SDRAM Input AC Timing Specifications

At recommended operating conditions with GV_{DD} of 2.5 V ± 5%.

Parameter	Symbol	Min	Max	Unit	Notes
AC input low voltage	V_{IL}	—	MV_{REF} – 0.31	V	
AC input high voltage	V_{IH}	MV_{REF} + 0.31	GV_{DD} + 0.3	V	
MDQS—MDQ/MECC input skew per byte	t_{DISKEW}	—		ps	1
333 MHz			750		
266 MHz			1125		

Note:

1. Maximum possible skew between a data strobe (MDQS[n]) and any corresponding bit of data (MDQ[8n + {0...7}] if 0 <= n <= 7) or ECC (MECC[{0...7}] if n = 8).

Figure 4 illustrates the DDR input timing diagram showing the t_{DISKEW} timing parameter.

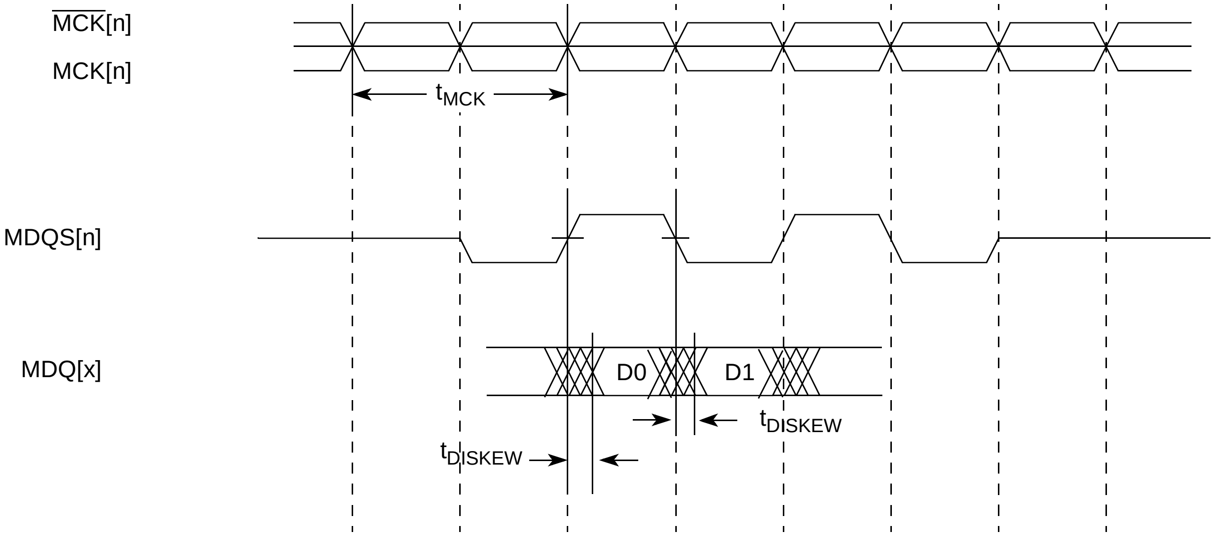


Figure 4. DDR Input Timing Diagram

6.2.2 DDR SDRAM Output AC Timing Specifications

Table 14 and Table 15 provide the output AC timing specifications and measurement conditions for the DDR SDRAM interface.

Figure 8 shows the GMII transmit AC timing diagram.

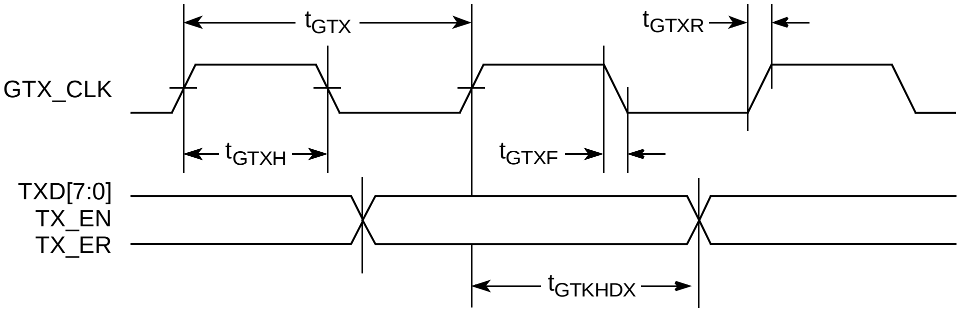


Figure 8. GMII Transmit AC Timing Diagram

8.2.1.2 GMII Receive AC Timing Specifications

Table 22 provides the GMII receive AC timing specifications.

Table 22. GMII Receive AC Timing Specifications

At recommended operating conditions with LV_{DD}/OV_{DD} of 3.3 V ± 10%.

Parameter/Condition	Symbol[1]	Min	Typ	Max	Unit
RX_CLK clock period	t_{GRX}	—	8.0	—	ns
RX_CLK duty cycle	t_{GRXH}/t_{GRX}	40	—	60	%
RXD[7:0], RX_DV, RX_ER setup time to RX_CLK	t_{GRDVKH}	2.0	—	—	ns
RXD[7:0], RX_DV, RX_ER hold time to RX_CLK	t_{GRDXKH}	0.5	—	—	ns
RX_CLK clock rise, V_{IL}(min) to V_{IH}(max)	t_{GRXR}	—	—	1.0	ns
RX_CLK clock fall time, V_{IH}(max) to V_{IL}(min)	t_{GRXF}	—	—	1.0	ns

Note:

1. The symbols for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{GRDVKH} symbolizes GMII receive timing (GR) with respect to the time data input signals (D) reaching the valid state (V) relative to the t_{RX} clock reference (K) going to the high state (H) or setup time. Also, t_{GRDXKL} symbolizes GMII receive timing (GR) with respect to the time data input signals (D) went invalid (X) relative to the t_{GRX} clock reference (K) going to the low (L) state or hold time. In general, the clock reference symbol is based on three letters representing the clock of a particular function. For example, the subscript of t_{GRX} represents the GMII (G) receive (RX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

Figure 14 shows the TBI receive AC timing diagram.

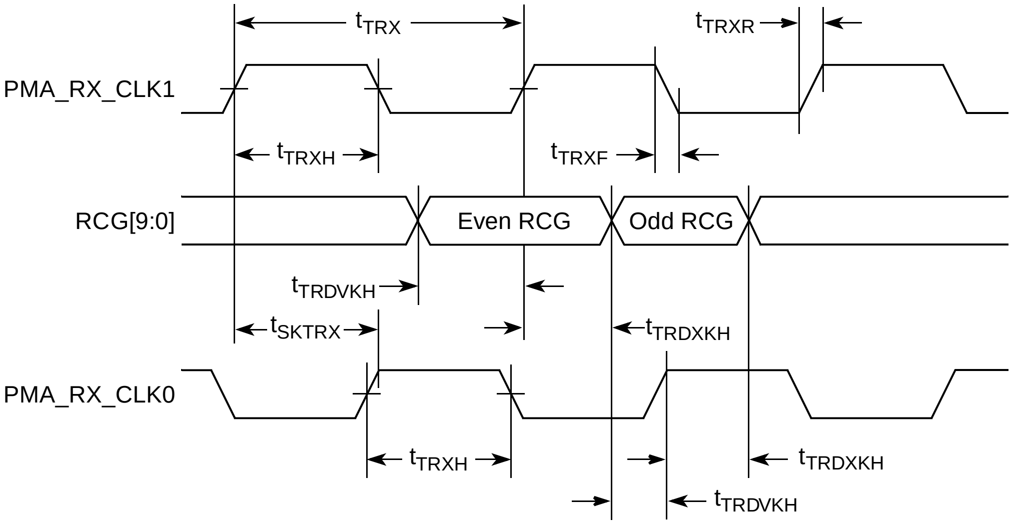


Figure 14. TBI Receive AC Timing Diagram

8.2.4 RGMII and RTBI AC Timing Specifications

Table 27 presents the RGMII and RTBI AC timing specifications.

Table 27. RGMII and RTBI AC Timing Specifications

At recommended operating conditions with LV_{DD} of 2.5 V ± 5%.

Parameter/Condition	Symbol[1]	Min	Typ	Max	Unit
Data to clock output skew (at transmitter)	t_{SKRGT}	–0.5	—	0.5	ns
Data to clock input skew (at receiver)[2]	t_{SKRGT}	1.0	—	2.8	ns
Clock cycle duration[3]	t_{RGT}	7.2	8.0	8.8	ns
Duty cycle for 1000Base-T[4, 5]	t_{RGTH}/t_{RGT}	45	50	55	%
Duty cycle for 10BASE-T and 100BASE-TX[3, 5]	t_{RGTH}/t_{RGT}	40	50	60	%
Rise time (20%–80%)	t_{RGTR}	—	—	0.75	ns
Fall time (20%–80%)	t_{RGTF}	—	—	0.75	ns
GTX_CLK125 reference clock period	t_{G12}[6]	—	8.0	—	ns
GTX_CLK125 reference clock duty cycle	t_{G125H}/t_{G125}	47	—	53	%

Notes:

1. In general, the clock reference symbol for this section is based on the symbols RGT to represent RGMII and RTBI timing. For example, the subscript of t_{RGT} represents the TBI (T) receive (RX) clock. Also, the notation for rise (R) and fall (F) times follows the clock symbol. For symbols representing skews, the subscript is SK followed by the clock being skewed (RGT).
2. This implies that PC board design requires clocks to be routed so that an additional trace delay of greater than 1.5 ns is added to the associated clock signal.
3. For 10 and 100 Mbps, t_{RGT} scales to 400 ns ± 40 ns and 40 ns ± 4 ns, respectively.
4. Duty cycle may be stretched/shrunk during speed changes or while transitioning to a received packet clock domains as long as the minimum duty cycle is not violated and stretching occurs for no more than three t_{RGT} of the lowest speed transitioned.
5. Duty cycle reference is $LV_{DD}/2$.
6. This symbol represents the external GTX_CLK125 and does not follow the original symbol naming convention.

Figure 15 shows the RBMII and RTBI AC timing and multiplexing diagrams.

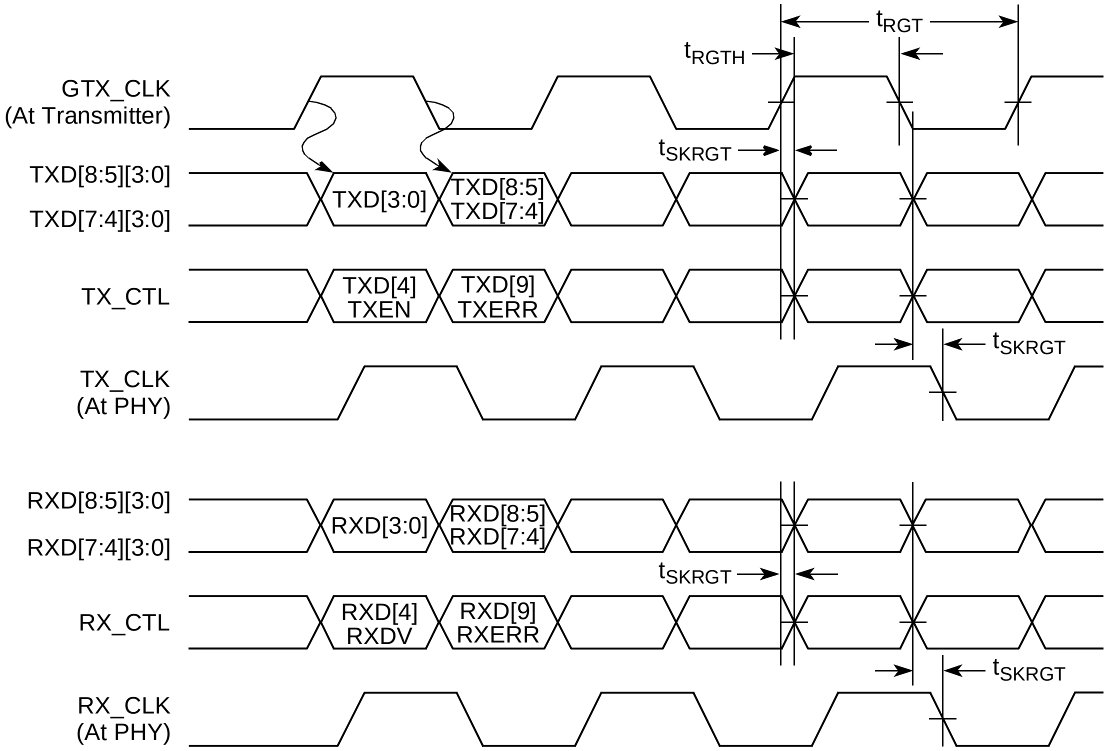


Figure 15. RGMII and RTBI AC Timing and Multiplexing Diagrams

10 Local Bus

This section describes the DC and AC electrical specifications for the local bus interface of the MPC8347E.

10.1 Local Bus DC Electrical Characteristics

Table 33 provides the DC electrical characteristics for the local bus interface.

Table 33. Local Bus DC Electrical Characteristics

Parameter	Symbol	Min	Max	Unit
High-level input voltage	V_{IH}	2	OV_{DD} + 0.3	V
Low-level input voltage	V_{IL}	–0.3	0.8	V
Input current	I_{IN}	—	±5	μA
High-level output voltage, I_{OH} = –100 μA	V_{OH}	OV_{DD} – 0.2	—	V
Low-level output voltage, I_{OL} = 100 μA	V_{OL}	—	0.2	V

10.2 Local Bus AC Electrical Specification

Table 34 and Table 35 describe the general timing parameters of the local bus interface of the MPC8347E.

Table 34. Local Bus General Timing Parameters—DLL On

Parameter	Symbol[1]	Min	Max	Unit	Notes
Local bus cycle time	t_{LBK}	7.5	—	ns	2
Input setup to local bus clock (except LUPWAIT)	$t_{LBIVKH1}$	1.5	—	ns	3, 4
LUPWAIT input setup to local bus clock	$t_{LBIVKH2}$	2.2	—	ns	3, 4
Input hold from local bus clock (except LUPWAIT)	$t_{LBIXKH1}$	1.0	—	ns	3, 4
LUPWAIT Input hold from local bus clock	$t_{LBIXKH2}$	1.0	—	ns	3, 4
LALE output fall to LAD output transition (LATCH hold time)	$t_{LBOTOT1}$	1.5	—	ns	5
LALE output fall to LAD output transition (LATCH hold time)	$t_{LBOTOT2}$	3	—	ns	6
LALE output fall to LAD output transition (LATCH hold time)	$t_{LBOTOT3}$	2.5	—	ns	7
Local bus clock to LALE rise	t_{LBKHLR}	—	4.5	ns	
Local bus clock to output valid (except LAD/LDP and LALE)	$t_{LBKHOV1}$	—	4.5	ns	
Local bus clock to data valid for LAD/LDP	$t_{LBKHOV2}$	—	4.5	ns	3
Local bus clock to address valid for LAD	$t_{LBKHOV3}$	—	4.5	ns	3
Output hold from local bus clock (except LAD/LDP and LALE)	$t_{LBKHOX1}$	1	—	ns	3

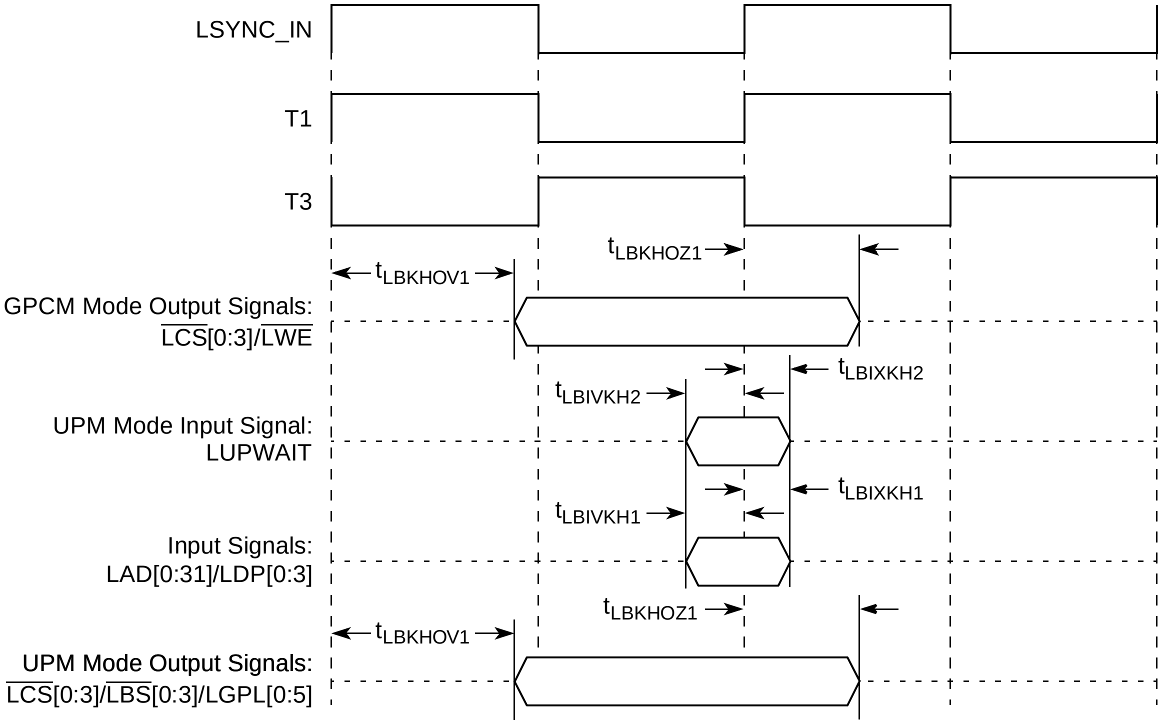


Figure 22. Local Bus Signals, GPCM/UPM Signals for LCCR[CLKDIV] = 2 (DLL Enabled)

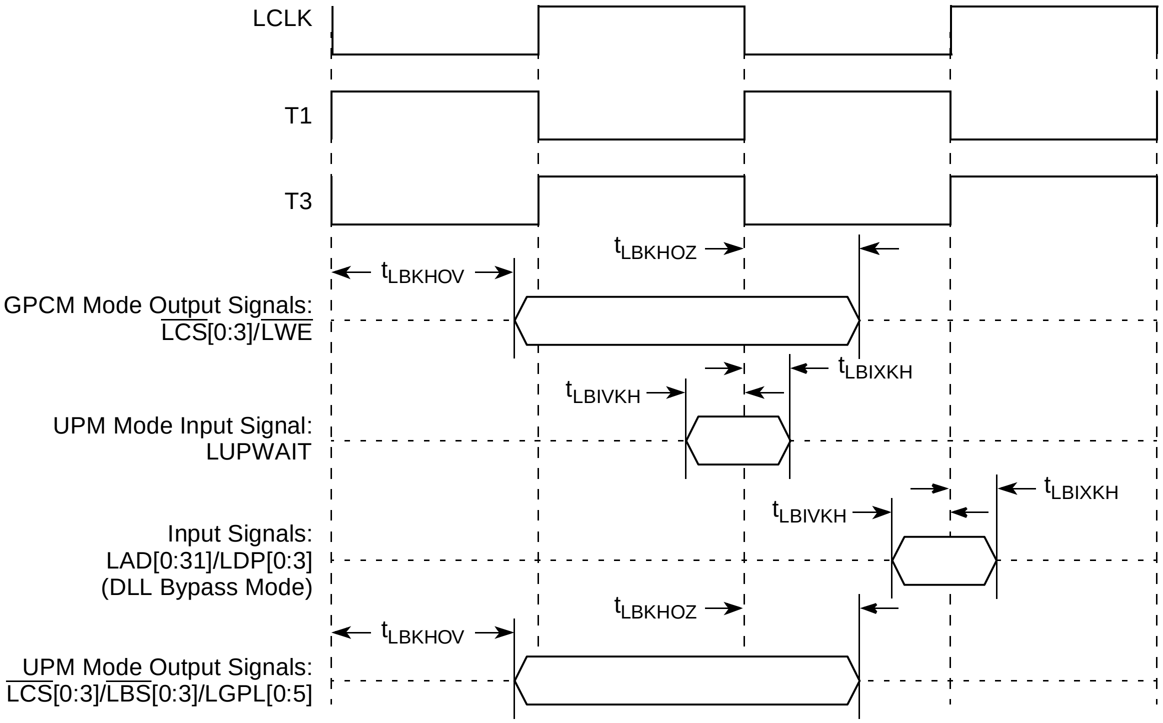


Figure 23. Local Bus Signals, GPCM/UPM Signals for LCCR[CLKDIV] = 2 (DLL Bypass Mode)

16 IPIC

This section describes the DC and AC electrical specifications for the external interrupt pins.

16.1 IPIC DC Electrical Characteristics

Table 47 provides the DC electrical characteristics for the external interrupt pins.

Table 47. IPIC DC Electrical Characteristics[1]

Characteristic	Symbol	Condition	Min	Max	Unit	Notes
Input high voltage	V_{IH}		2.0	OV_{DD} + 0.3	V	
Input low voltage	V_{IL}		–0.3	0.8	V	
Input current	I_{IN}			±5	μA	
Output low voltage	V_{OL}	I_{OL} = 8.0 mA	—	0.5	V	2
Output low voltage	V_{OL}	I_{OL} = 3.2 mA	—	0.4	V	2

Notes:

1. This table applies for pins $\overline{\text{IRQ}}$[0:7], $\overline{\text{IRQ\_OUT}}$, and $\overline{\text{MCP\_OUT}}$.
2. $\overline{\text{IRQ\_OUT}}$ and $\overline{\text{MCP\_OUT}}$ are open-drain pins; thus V_{OH} is not relevant for those pins.

16.2 IPIC AC Timing Specifications

Table 48 provides the IPIC input and output AC timing specifications.

Table 48. IPIC Input AC Timing Specifications[1]

Characteristic	Symbol[2]	Min	Unit
IPIC inputs—minimum pulse width	t_{PICWID}	20	ns

Notes:

1. Input specifications are measured at the 50 percent level of the IPIC input signals. Timings are measured at the pin.
2. IPIC inputs and outputs are asynchronous to any visible clock. IPIC outputs should be synchronized before use by external synchronous logic. IPIC inputs must be valid for at least t_{PICWID} ns to ensure proper operation in edge triggered mode.

Table 51. MPC8347E (TBGA) Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
MPH1_NXT/DR_SESS_VLD_NXT	D27	I	OV_{DD}	
MPH1_DIR_DPPULLUP/ DR_XCVR_SEL_DPPULLUP	A28	I/O	OV_{DD}	
MPH1_STP_SUSPEND/ DR_STP_SUSPEND	F26	O	OV_{DD}	
MPH1_PWRFAULT/ DR_RX_ERROR_PWRFAULT	E27	I	OV_{DD}	
MPH1_PCTL0/DR_TX_VALID_PCTL0	A29	O	OV_{DD}	
MPH1_PCTL1/DR_TX_VALIDH_PCTL1	D28	O	OV_{DD}	
MPH1_CLK/DR_CLK	B29	I	OV_{DD}	
USB Port 0				
MPH0_D0_ENABLEN/DR_D8_CHGVBUS	C29	I/O	OV_{DD}	
MPH0_D1_SER_TXD/DR_D9_DCHGVBUS	A30	I/O	OV_{DD}	
MPH0_D2_VMO_SE0/DR_D10_DPPD	E28	I/O	OV_{DD}	
MPH0_D3_SPEED/DR_D11_DMMD	B30	I/O	OV_{DD}	
MPH0_D4_DP/DR_D12_VBUS_VLD	C30	I/O	OV_{DD}	
MPH0_D5_DM/DR_D13_SESS_END	A31	I/O	OV_{DD}	
MPH0_D6_SER_RCV/DR_D14	B31	I/O	OV_{DD}	
MPH0_D7_DRVVBUS/DR_D15_IDPULLUP	C31	I/O	OV_{DD}	
MPH0_NXT/DR_RX_ACTIVE_ID	B32	I	OV_{DD}	
MPH0_DIR_DPPULLUP/DR_RESET	A32	I/O	OV_{DD}	
MPH0_STP_SUSPEND/DR_TX_READY	A33	I/O	OV_{DD}	
MPH0_PWRFAULT/DR_RX_VALIDH	C32	I	OV_{DD}	
MPH0_PCTL0/DR_LINE_STATE0	D31	I/O	OV_{DD}	
MPH0_PCTL1/DR_LINE_STATE1	E30	I/O	OV_{DD}	
MPH0_CLK/DR_RX_VALID	B33	I	OV_{DD}	
Programmable Interrupt Controller				
$\overline{\text{MCP\_OUT}}$	AN33	O	OV_{DD}	2
$\overline{\text{IRQ}}$0/$\overline{\text{MCP_IN}}$/GPIO2[12]	C19	I/O	OV_{DD}	
$\overline{\text{IRQ}}$[1:5]/GPIO2[13:17]	C22, A22, D21, C21, B21	I/O	OV_{DD}	
$\overline{\text{IRQ}}$[6]/GPIO2[18]/CKSTOP_OUT	A21	I/O	OV_{DD}	
$\overline{\text{IRQ}}$[7]/GPIO2[19]/CKSTOP_IN	C20	I/O	OV_{DD}	
Ethernet Management Interface				
EC_MDC	A7	O	LV_{DD1}	
EC_MDIO	E9	I/O	LV_{DD1}	2

Table 51. MPC8347E (TBGA) Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
Gigabit Reference Clock				
EC_GTX_CLK125	C8	I	LV_{DD1}	
Three-Speed Ethernet Controller (Gigabit Ethernet 1)				
TSEC1_COL/GPIO2[20]	A17	I/O	OV_{DD}	
TSEC1_CRS/GPIO2[21]	F12	I/O	LV_{DD1}	
TSEC1_GTX_CLK	D10	O	LV_{DD1}	3
TSEC1_RX_CLK	A11	I	LV_{DD1}	
TSEC1_RX_DV	B11	I	LV_{DD1}	
TSEC1_RX_ER/GPIO2[26]	B17	I/O	OV_{DD}	
TSEC1_RXD[7:4]/GPIO2[22:25]	B16, D16, E16, F16	I/O	OV_{DD}	
TSEC1_RXD[3:0]	E10, A8, F10, B8	I	LV_{DD1}	
TSEC1_TX_CLK	D17	I	OV_{DD}	
TSEC1_TXD[7:4]/GPIO2[27:30]	A15, B15, A14, B14	I/O	OV_{DD}	
TSEC1_TXD[3:0]	A10, E11, B10, A9	O	LV_{DD1}	11
TSEC1_TX_EN	B9	O	LV_{DD1}	
TSEC1_TX_ER/GPIO2[31]	A16	I/O	OV_{DD}	
Three-Speed Ethernet Controller (Gigabit Ethernet 2)				
TSEC2_COL/GPIO1[21]	C14	I/O	OV_{DD}	
TSEC2_CRS/GPIO1[22]	D6	I/O	LV_{DD2}	
TSEC2_GTX_CLK	A4	O	LV_{DD2}	
TSEC2_RX_CLK	B4	I	LV_{DD2}	
TSEC2_RX_DV/GPIO1[23]	E6	I/O	LV_{DD2}	
TSEC2_RXD[7:4]/GPIO1[26:29]	A13, B13, C13, A12	I/O	OV_{DD}	
TSEC2_RXD[3:0]/GPIO1[13:16]	D7, A6, E8, B7	I/O	LV_{DD2}	
TSEC2_RX_ER/GPIO1[25]	D14	I/O	OV_{DD}	
TSEC2_TXD[7]/GPIO1[31]	B12	I/O	OV_{DD}	
TSEC2_TXD[6]/DR_XCVR_TERM_SEL	C12	O	OV_{DD}	
TSEC2_TXD[5]/DR_UTMI_OPMODE1	D12	O	OV_{DD}	
TSEC2_TXD[4]/DR_UTMI_OPMODE0	E12	O	OV_{DD}	
TSEC2_TXD[3:0]/GPIO1[17:20]	B5, A5, F8, B6	I/O	LV_{DD2}	
TSEC2_TX_ER/GPIO1[24]	F14	I/O	OV_{DD}	
TSEC2_TX_EN/GPIO1[12]	C5	I/O	LV_{DD2}	3
TSEC2_TX_CLK/GPIO1[30]	E14	I/O	OV_{DD}	

Table 52. MPC8347E (PBGA) Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
PCI1_IRDY	E13	I/O	OV_{DD}	5
PCI1_STOP	C13	I/O	OV_{DD}	5
PCI1_DEVSEL	B13	I/O	OV_{DD}	5
PCI1_IDSEL	C17	I	OV_{DD}	
PCI1_SERR	C12	I/O	OV_{DD}	5
PCI1_PERR	B12	I/O	OV_{DD}	5
PCI1_REQ[0]	A21	I/O	OV_{DD}	
PCI1_REQ[1]/CPCI1_HS_ES	C19	I	OV_{DD}	
PCI1_REQ[2:4]	C18, A19, E20	I	OV_{DD}	
PCI1_GNT0	B20	I/O	OV_{DD}	
PCI1_GNT1/CPCI1_HS_LED	C20	O	OV_{DD}	
PCI1_GNT2/CPCI1_HS_ENUM	B19	O	OV_{DD}	
PCI1_GNT[3:4]	A20, E18	O	OV_{DD}	
M66EN	L26	I	OV_{DD}	
DDR SDRAM Memory Interface				
MDQ[0:63]	AC25, AD27, AD25, AH27, AE28, AD26, AD24, AF27, AF25, AF28, AH24, AG26, AE25, AG25, AH26, AH25, AG22, AH22, AE21, AD19, AE22, AF23, AE19, AG20, AG19, AD17, AE16, AF16, AF18, AG18, AH17, AH16, AG9, AD12, AG7, AE8, AD11, AH9, AH8, AF6, AF8, AE6, AF1, AE4, AG8, AH3, AG3, AG4, AH2, AD7, AB4, AB3, AG1, AD5, AC2, AC1, AC4, AA3, Y4, AA4, AB1, AB2, Y5, Y3	I/O	GV_{DD}	
MECC[0:4]/MSRCID[0:4]	AG13, AE14, AH12, AH10, AE15	I/O	GV_{DD}	
MECC[5]/MDVAL	AH14	I/O	GV_{DD}	
MECC[6:7]	AE13, AH11	I/O	GV_{DD}	
MDM[0:8]	AG28, AG24, AF20, AG17, AE9, AH5, AD1, AA2, AG12	O	GV_{DD}	
MDQS[0:8]	AE27, AE26, AE20, AH18, AG10, AF5, AC3, AA1, AH13	I/O	GV_{DD}	
MBA[0:1]	AF10, AF11	O	GV_{DD}	
MA[0:14]	AF13, AF15, AG16, AD16, AF17, AH20, AH19, AH21, AD18, AG21, AD13, AF21, AF22, AE1, AA5	O	GV_{DD}	
MWE	AD10	O	GV_{DD}	
MRAS	AF7	O	GV_{DD}	

Table 54 provides the operating frequencies for the MPC8347E TBGA under recommended operating conditions (see Table 2).

Table 54. Operating Frequencies for TBGA

Characteristic[1]	400 MHz	533 MHz	667 MHz	Unit
e300 core frequency (*core_clk*)	266–400	266–533	266–667	MHz
Coherent system bus frequency (*csb_clk*)	100–266	100–266	100–333	MHz
DDR and memory bus frequency (MCLK)[2]	100–133	100–133	100–166.67	MHz
Local bus frequency (LCLK*n*)[3]	16.67–133	16.67–133	16.67–133	MHz
PCI input frequency (CLKIN or PCI_CLK)	25–66	25–66	25–66	MHz
Security core maximum internal operating frequency	133	133	166	MHz
USB_DR, USB_MPH maximum internal operating frequency	133	133	166	MHz

[1] The CLKIN frequency, RCWL[SPMF], and RCWL[COREPLL] settings must be chosen so that the resulting *csb_clk*, MCLK, LCLK[0:2], and *core_clk* frequencies do not exceed their respective maximum or minimum operating frequencies. The value of SCCR[ENCCM], SCCR[USBDRCM], and SCCR[USBMPHCM] must be programmed so that the maximum internal operating frequency of the Security core and USB modules does not exceed the respective values listed in this table.

[2] The DDR data rate is 2x the DDR memory bus frequency.

[3] The local bus frequency is 1/2, 1/4, or 1/8 of the *lbiu_clk* frequency (depending on LCCR[CLKDIV]) which is in turn 1x or 2x the *csb_clk* frequency (depending on RCWL[LBIUCM]).

Table 55 provides the operating frequencies for the MPC8347E PBGA under recommended operating conditions.

Table 55. Operating Frequencies for PBGA

Characteristic[1]	266 MHz	333 MHz	400 MHz	Unit
e300 core frequency (*core_clk*)	200–266	200–333	200–400	MHz
Coherent system bus frequency (*csb_clk*)	100–266			MHz
Local bus frequency (LCLK*n*)[2]	16.67–133			MHz
PCI input frequency (CLKIN or PCI_CLK)	25–66			MHz
Security core maximum internal operating frequency	133			MHz
USB_DR, USB_MPH maximum internal operating frequency	133			MHz

[1] The CLKIN frequency, RCWL[SPMF], and RCWL[COREPLL] settings must be chosen so that the resulting *csb_clk*, MCLK, LCLK[0:2], and *core_clk* frequencies do not exceed their respective maximum or minimum operating frequencies. The value of SCCR[ENCCM], SCCR[USBDRCM], and SCCR[USBMPHCM] must be programmed so that the maximum internal operating frequency of the Security core and USB modules does not exceed the respective values listed in this table.

[2] The local bus frequency is 1/2, 1/4, or 1/8 of the *lbiu_clk* frequency (depending on LCCR[CLKDIV]) which is in turn 1x or 2x the *csb_clk* frequency (depending on RCWL[LBIUCM]).

Table 58. CSB Frequency Options for Agent Mode

CFG_CLKIN_DIV at Reset[1]	SPMF	*csb_clk* : Input Clock Ratio[2]	Input Clock Frequency (MHz)[2]			
			16.67	**25**	**33.33**	**66.67**
			csb_clk **Frequency (MHz)**			
Low	0010	2 : 1				133
Low	0011	3 : 1			100	200
Low	0100	4 : 1		100	133	266
Low	0101	5 : 1		125	166	333
Low	0110	6 : 1	100	150	200	
Low	0111	7 : 1	116	175	233	
Low	1000	8 : 1	133	200	266	
Low	1001	9 : 1	150	225	300	
Low	1010	10 : 1	166	250	333	
Low	1011	11 : 1	183	275		
Low	1100	12 : 1	200	300		
Low	1101	13 : 1	216	325		
Low	1110	14 : 1	233			
Low	1111	15 : 1	250			
Low	0000	16 : 1	266			
High	0010	4 : 1		100	133	266
High	0011	6 : 1	100	150	200	
High	0100	8 : 1	133	200	266	
High	0101	10 : 1	166	250	333	
High	0110	12 : 1	200	300		
High	0111	14 : 1	233			
High	1000	16 : 1	266			

[1] CFG_CLKIN_DIV doubles csb_clk if set high.

[2] CLKIN is the input clock in host mode; PCI_CLK is the input clock in agent mode.

DDR2 memory may be used at 133 MHz provided that the memory components are specified for operation at this frequency.

19.2 Core PLL Configuration

RCWL[COREPLL] selects the ratio between the internal coherent system bus clock (*csb_clk*) and the e300 core clock (*core_clk*). Table 59 shows the encodings for RCWL[COREPLL]. COREPLL values that are not listed in Table 59 should be considered as reserved.

Table 62. Package Thermal Characteristics for PBGA (continued)

Characteristic	Symbol	Value	Unit	Notes
Junction-to-case thermal	$R_{\theta JC}$	5	°C/W	5
Junction-to-package natural convection on top	Ψ_{JT}	5	°C/W	6

Notes

1. Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, air flow, power dissipation of other components on the board, and board thermal resistance.
2. Per SEMI G38-87 and JEDEC JESD51-2 with the single-layer board horizontal.
3. Per JEDEC JESD51-6 with the board horizontal.
4. Thermal resistance between the die and the printed-circuit board per JEDEC JESD51-8. Board temperature is measured on the top surface of the board near the package.
5. Thermal resistance between the die and the case top surface as measured by the cold plate method (MIL SPEC-883 Method 1012.1).
6. Thermal characterization parameter indicating the temperature difference between package top and the junction temperature per JEDEC JESD51-2. When Greek letters are not available, the thermal characterization parameter is written as Psi-JT.

20.2 Thermal Management Information

For the following sections, $P_D = (V_{DD} \times I_{DD}) + P_{I/O}$ where $P_{I/O}$ is the power dissipation of the I/O drivers. See Table 5 for I/O power dissipation values.

20.2.1 Estimation of Junction Temperature with Junction-to-Ambient Thermal Resistance

An estimation of the chip junction temperature, T_J, can be obtained from the equation:

$$T_J = T_A + (R_{\theta JA} \times P_D)$$

where:

T_J = junction temperature (°C)

T_A = ambient temperature for the package (°C)

$R_{\theta JA}$ = junction-to-ambient thermal resistance (°C/W)

P_D = power dissipation in the package (W)

The junction-to-ambient thermal resistance is an industry-standard value that provides a quick and easy estimation of thermal performance. Generally, the value obtained on a single-layer board is appropriate for a tightly packed printed-circuit board. The value obtained on the board with the internal planes is usually appropriate if the board has low power dissipation and the components are well separated. Test cases have demonstrated that errors of a factor of two (in the quantity $T_J – T_A$) are possible.

20.2.2 Estimation of Junction Temperature with Junction-to-Board Thermal Resistance

The thermal performance of a device cannot be adequately predicted from the junction-to-ambient thermal resistance. The thermal performance of any component is strongly dependent on the power dissipation of surrounding components. In addition, the ambient temperature varies widely within the application. For many natural convection and especially closed box applications, the board temperature at the perimeter (edge) of the package is approximately the same as the local air temperature near the device. Specifying the local ambient conditions explicitly as the board temperature provides a more precise description of the local ambient conditions that determine the temperature of the device.

At a known board temperature, the junction temperature is estimated using the following equation:

$$T_J = T_A + (R_{\theta JA} \times P_D)$$

where:

T_J = junction temperature (°C)

T_A = ambient temperature for the package (°C)

$R_{\theta JA}$ = junction-to-ambient thermal resistance (°C/W)

P_D = power dissipation in the package (W)

When the heat loss from the package case to the air can be ignored, acceptable predictions of junction temperature can be made. The application board should be similar to the thermal test condition: the component is soldered to a board with internal planes.

20.2.3 Experimental Determination of Junction Temperature

To determine the junction temperature of the device in the application after prototypes are available, use the thermal characterization parameter (Ψ_{JT}) to determine the junction temperature and a measure of the temperature at the top center of the package case using the following equation:

$$T_J = T_T + (\Psi_{JT} \times P_D)$$

where:

T_J = junction temperature (°C)

T_T = thermocouple temperature on top of package (°C)

Ψ_{JT} = junction-to-ambient thermal resistance (°C/W)

P_D = power dissipation in the package (W)

The thermal characterization parameter is measured per the JESD51-2 specification using a 40 gauge type T thermocouple epoxied to the top center of the package case. The thermocouple should be positioned so that the thermocouple junction rests on the package. A small amount of epoxy is placed over the thermocouple junction and over about 1 mm of wire extending from the junction. The thermocouple wire is placed flat against the package case to avoid measurement errors caused by cooling effects of the thermocouple wire.

20.2.4 Heat Sinks and Junction-to-Case Thermal Resistance

Some application environments require a heat sink to provide the necessary thermal management of the device. When a heat sink is used, the thermal resistance is expressed as the sum of a junction-to-case thermal resistance and a case-to-ambient thermal resistance:

$$R_{\theta JA} = R_{\theta JC} + R_{\theta CA}$$

the large value of the pull-up/pull-down resistor should minimize the disruption of signal quality or speed for the output pins.

21.7 Pull-Up Resistor Requirements

The MPC8347E requires high resistance pull-up resistors (10 kΩ is recommended) on open-drain pins, including I^{2}C pins, the Ethernet Management MDIO pin, and IPIC interrupt pins.

For more information on required pull-up resistors and the connections required for the JTAG interface, refer to application note AN2931, *PowerQUICC™ Design Checklist*.

Table 66. Document Revision History (continued)

Revision	Date	Substantive Change(s)
8	2/2007	Page 1, updated first paragraph to reflect PowerQUICC II information. Updated note after second paragraph. In the features list in Section 1, “Overview,” corrected DDR data rate to show: • 266 MHz for PBGA parts for all silicon revisions • 333 MHz for DDR for TBGA parts for silicon Rev. 1.x In Table 5, “MPC8347E Typical I/O Power Dissipation,” added GV_{DD} 1.8-V values for DDR2; added table footnote to designate rates that apply only to the TBGA package. In Figure 43, “JTAG Interface Connection,” updated with new figure. In Section 23, “Ordering Information,” replicated note from document introduction. In Section 23.1, “Part Numbers Fully Addressed by This Document,” replaced third sentence of first paragraph directing customer to product summary page for available frequency configuration parts. Updated back page information.
7	8/2006	Changed all references to revision 2.0 silicon to revision 3.0 silicon. Changed V_{IH} minimum value in Table 36, “JTAG Interface DC Electrical Characteristics,” to OV_{DD} – 0.3. In Table 60, “Suggested PLL Configurations,” deleted reference-number rows 902 and 703.
6	3/2006	Section 2, “Electrical Characteristics,” moved to second section and all other section, table, and figure numbering change accordingly. Table 7, “CLKIN AC Timing Specifications:” Changed max rise and fall time from 1.2 to 2.3. Table 22, “GMII Receive AC Timing Specifications:” Changed min t_{TTKHDX} from 0.5 to 1.0. Table 30, “MII Management AC Timing Specifications:” Changed max value of t_{MDKHDX} from 70 to 170. Table 34, “Local Bus General Timing Parameters—DLL on:” Changed min $t_{LBIVKH2}$ from 1.7 to 2.2. Table 36, “JTAG interface DC Electrical Characteristics:” Changed V_{IH} input high voltage min to 2.0. Table 54, “Operating Frequencies for TBGA:” • Updated TBD values. • Changed maximum coherent system bus frequency for TBGA 667-MHz device to 333 MHz. Table 55, “Operating Frequencies for PBGA:” • Updated TBD values. • Changed PBGA maximum coherent system bus frequency to 266 MHz, and maximum DDR memory bus frequency to 133 MHz. Table 60, “Suggested PLL Configurations”: Removed some values from suggested PLL configurations for reference numbers 902, 922, 903, and 923. Table 67, “Part Numbering Nomenclature”: Updated TBD values in note 1. Added Table 68, “SVR Settings.” Added Section 23.2, “Part Marking.”
5	10/2005	In Table 57, updated AAVID 30x30x9.4 mm Pin Fin (natural convection) junction-to-ambient thermal resistance, from 11 to 10.
4	9/2005	Added Table 2, “MPC8347E Typical I/O Power Dissipation.”
3	8/2005	Table 1: Updated values for power dissipation that were TBD in Revision 2.
2	5/2005	Table 1: Typical values for power dissipation are changed to TBD. Table 48: Footnote numbering was wrong. THERM0 should have footnote 9 instead of 8.

Table 66. Document Revision History (continued)

Revision	Date	Substantive Change(s)
1	4/2005	Table 1: Addition of note 1 Table 48: Addition of Therm0 (K32) Table 49: Addition of Therm0 (B15)
0	4/2005	Initial release.